Low-Voltage CMOS Octal Transparent Latch

With 5 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The MC74LCX373 is a high performance, non–inverting octal transparent latch operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5 V allows MC74LCX373 inputs to be safely driven from 5 V devices.

The MC74LCX373 contains 8 D-type latches with 3-state outputs. When the Latch Enable (LE) input is HIGH, data on the Dn inputs enters the latches. In this condition, the latches are transparent, i.e., a latch output will change state each time its D input changes. When LE is LOW, the latches store the information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE. The 3-state standard outputs are controlled by the Output Enable (\overline{OE}) input. When \overline{OE} is LOW, the standard outputs are enabled. When \overline{OE} is HIGH, the standard outputs are in the high impedance state, but this does not interfere with new data entering into the latches.

Features

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- · Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0 V$
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in all Three Logic States (10 μA)
 Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance:
 - Human Body Model >2000 V
 - ◆ Machine Model >200 V
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



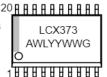
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MARKING DIAGRAMS

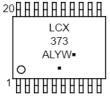


SOIC-20 WB DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E



LCX373 = Specific Device Code A = Assembly Location

L, WL = Wafer Lot Y, YY = Year

W, WW = Work Week
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

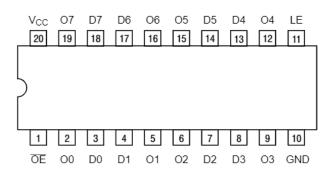


Figure 1. Pinout (Top View)

PIN NAMES

| PINS FUNCTION | | |
|-------------------|-----------------------|--|
| ŌĒ | Output Enable Input | |
| LE | Latch Enable Input | |
| D0-D7 Data Inputs | | |
| 00-07 | 3-State Latch Outputs | |

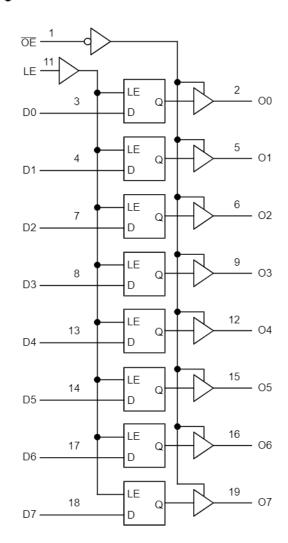


Figure 2. Logic Diagram

TRUTH TABLE

| | INPUTS | | OUTPUTS | |
|----|--------|----|---------|--|
| OE | LE | Dn | On | OPERATING MODE |
| L | H | H | H | Transparent (Latch Disabled); Read Latch |
| L | H | L | L | |
| L | L | h | H | Latched (Latch Enabled) Read Latch |
| L | L | I | L | |
| L | L | Х | NC | Hold; Read Latch |
| Н | L | Х | Z | Hold; Disabled Outputs |
| H | H | H | Z | Transparent (Latch Disabled); Disabled Outputs |
| H | H | L | Z | |
| H | L | h | Z | Latched (Latch Enabled); Disabled Outputs |
| H | L | I | Z | |

H = High Voltage Level

h = High Voltage Level One Setup Time Prior to the Latch Enable High-to-Low Transition

L = Low Voltage Level

= Low Voltage Level One Setup Time Prior to the Latch Enable High-to-Low Transition

NC = No Change, State Prior to the Latch Enable High-to-Low Transition

X = High or Low Voltage Level or Transitions are Acceptable

Z = High Impedance State

For I_{CC} Reasons DO NOT FLOAT Inputs

MAXIMUM RATINGS

| Symbol | Parameter | Value | Condition | Units |
|------------------|----------------------------------|-----------------------------------|--------------------------------------|-------|
| V _{CC} | DC Supply Voltage | -0.5 to +7.0 | | V |
| VI | DC Input Voltage | $-0.5 \le V_1 \le +7.0$ | | V |
| Vo | DC Output Voltage | $-0.5 \le V_0 \le +7.0$ | Output in 3-State | V |
| | | $-0.5 \le V_{O} \le V_{CC} + 0.5$ | Output in HIGH or LOW State (Note 1) | V |
| I _{IK} | DC Input Diode Current | -50 | V _I < GND | mA |
| I _{OK} | DC Output Diode Current | -50 | V _O < GND | mA |
| | | +50 | Vo > Vcc | mA |
| Io | DC Output Source/Sink Current | ±50 | | mA |
| Icc | DC Supply Current Per Supply Pin | ±100 | | mA |
| I _{GND} | DC Ground Current Per Ground Pin | ±100 | | mA |
| T _{STG} | Storage Temperature Range | -65 to +150 | | °C |
| MSL | Moisture Sensitivity | | Level 1 | |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Тур | Max | Units |
|-----------------|---|------------|----------------------|------------------------|-------|
| Vcc | Supply Voltage Operating Data Retention Only | 2.0 1.5 | 2.5, 3.3 2.5, 3.3 | 3.6 3.6 | V |
| VI | Input Voltage | 0 | | 5.5 | V |
| Vo | Output Voltage (HIGH or LOW State) (3-State) | 0 0 | | V _{CC} 5.5 | V |
| I _{OH} | HIGH Level Output Current V _{CC} = 3.0 V - 3.6 V V _{CC} = 2.7 V - 3.0 V V _{CC} = 2.3 V - 2.7 V | | | -24 -12 -8 | mA |
| I _{OL} | LOW Level Output Current V _{CC} = 3.0 V - 3.6 V V _{CC} = 2.7 V - 3.0 V V _{CC} = 2.3 V - 2.7 V | | | +24 +12 +8 | mA |
| T _A | Operating Free-Air Temperature | -40 | | +85 | °C |
| Δt/ΔV | Input Transition Rise or Fall Rate, V_{IN} from 0.8 V to 2.0 V, V_{CC} = 3.0 V | 0 | | 10 | ns/V |

DC ELECTRICAL CHARACTERISTICS

| | | | T _A = -40°C | to +85°C | |
|------------------|---------------------------------------|---|------------------------|----------|-------|
| Symbol | Characteristic | Condition | Min | Max | Units |
| V _{IH} | HIGH Level Input Voltage (Note 2) | 2.3 V ≤ V _{CC} ≤ 2.7 V | 1.7 | | V |
| | | 2.7 V ≤ V _{CC} ≤ 3.6 V | 2.0 | | 1 |
| V _{IL} | LOW Level Input Voltage (Note 2) | 2.3 V ≤ V _{CC} ≤ 2.7 V | | 0.7 | V |
| | | 2.7 V ≤ V _{CC} ≤ 3.6 V | | 0.8 | 1 |
| V _{OH} | HIGH Level Output Voltage | $2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}$; $I_{OL} = 100 \mu\text{A}$ | V _{CC} - 0.2 | | V |
| | | V _{CC} = 2.3 V; I _{OH} = -8 mA | 1.8 | | 1 |
| | | V _{CC} = 2.7 V; I _{OH} = −12 mA | 2.2 | | 1 |
| | | V _{CC} = 3.0 V; I _{OH} = -18 mA | 2.4 | | 1 |
| | | V _{CC} = 3.0 V; I _{OH} = -24 mA | 2.2 | | 1 |
| V _{OL} | LOW Level Output Voltage | $2.3 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}; \text{I}_{OL} = 100 \mu\text{A}$ | | 0.2 | V |
| | | V _{CC} = 2.3 V; I _{OL} = 8 mA | | 0.6 | 1 |
| | | V _{CC} = 2.7 V; I _{OL} = 12 mA | | 0.4 | 1 |
| | | V _{CC} = 3.0 V; I _{OL} = 16 mA | | 0.4 | 1 |
| | | V _{CC} = 3.0 V; I _{OL} = 24 mA | | 0.55 | 1 |
| I _{OZ} | 3-State Output Current | $V_{CC} = 3.6 \text{ V}, V_{IN} = V_{IH} \text{ or } V_{IL}, V_{OUT} = 0 \text{ to } 5.5 \text{ V}$ | | ±5 | μА |
| I _{OFF} | Power Off Leakage Current | V _{CC} = 0, V _{IN} = 5.5 V or V _{OUT} = 5.5 V | | 10 | μА |
| I _{IN} | Input Leakage Current | V _{CC} = 3.6 V, V _{IN} = 5.5 V or GND | | ±5 | μА |
| I _{CC} | Quiescent Supply Current | V _{CC} = 3.6 V, V _{IN} = 5.5 V or GND | | 10 | μΑ |
| ΔI_{CC} | Increase in I _{CC} per Input | $2.3 \le V_{CC} \le 3.6 \text{ V}; V_{IH} = V_{CC} - 0.6 \text{ V}$ | | 500 | μА |

^{2.} These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS ($t_R = t_F = 2.5 \text{ ns}; R_L = 500 \Omega$)

| | | | | | Lin | nits | | | |
|--------------------------------------|---|----------|-----------------------|-------------|-----------------------|------------|-----------------------|--------------|-------|
| | | | | | T _A = -40° | C to +85°C | | | |
| | | | V _{CC} = 3.3 | 3 V ± 0.3 V | V _{CC} = | 2.7 V | V _{CC} = 2.5 | V ± 0.2 V | 1 |
| | | | C _L = | 50 pF | C _L = | 50 pF | C _L = | 30 pF | 1 |
| Symbol | Parameter | Waveform | Min | Max | Min | Max | Min | Max | Units |
| t _{PLH} t _{PHL} | Propagation Delay D _n to O _n | 1 | 1.5 1.5 | 8.0 8.0 | 1.5 1.5 | 9.0 9.0 | 1.5 1.5 | 9.6 9.6 | ns |
| t _{PLH} t _{PHL} | Propagation Delay LE to O _n | 3 | 1.5 1.5 | 8.5 8.5 | 1.5 1.5 | 9.5 9.5 | 1.5 1.5 | 10.5 10.5 | ns |
| t _{PZH} t _{PZL} | Output Enable Time to HIGH and LOW Level | 2 | 1.5 1.5 | 8.5 8.5 | 1.5 1.5 | 9.5 9.5 | 1.5 1.5 | 10.5 10.5 | ns |
| t _{PHZ} | Output Disable Time From High and Low Level | 2 | 1.5 1.5 | 7.5 7.5 | 1.5 1.5 | 8.5 8.5 | 1.5 1.5 | 9.0 9.0 | ns |
| t _s | Setup Time, HIGH or LOW D _n to LE | 3 | 2.5 | | 2.5 | | 4.0 | | |
| t _h | Hold Time, HIGH or LOW D _n to LE | 3 | 1.5 | | 1.5 | | 2.0 | | |
| t _w | LE Pulse Width, HIGH | 3 | 3.3 | | 3.3 | | 4.0 | | |
| toshl toslh | Output-to-Output Skew (Note 3) | | | 1.0 1.0 | | | | | ns |

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

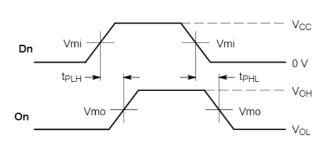
DYNAMIC SWITCHING CHARACTERISTICS

| | | | T, | A = +25° | С | |
|------------------|-------------------------------------|---|-----|--------------|-----|-------|
| Symbol | Characteristic | Condition | Min | Тур | Max | Units |
| V _{OLP} | Dynamic LOW Peak Voltage (Note 4) | V_{CC} = 3.3 V, C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V V_{CC} = 2.5 V, C_L = 30 pF, V_{IH} = 2.5 V, V_{IL} = 0 V | | 0.8 0.6 | | V |
| V _{OLV} | Dynamic LOW Valley Voltage (Note 4) | V_{CC} = 3.3 V, C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V V_{CC} = 2.5 V, C_L = 30 pF, V_{IH} = 2.5 V, V_{IL} = 0 V | | -0.8 -0.6 | | V |

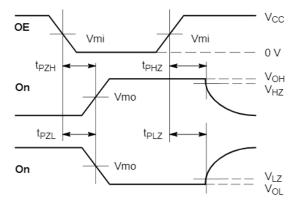
^{4.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

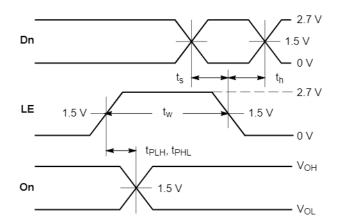
| Symbol | Parameter | Condition | Typical | Units |
|------------------|-------------------------------|--|---------|-------|
| C _{IN} | Input Capacitance | V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC} | 7 | pF |
| C _{I/O} | Input/Output Capacitance | V _{CC} = 3.3 V, V _I = 0 V or V _{CC} | 8 | pF |
| C _{PD} | Power Dissipation Capacitance | 10 MHz, V _{CC} = 3.3 V, V _I = 0 V or V _{CC} | 25 | pF |



WAVEFORM 1 – PROPAGATION DELAYS $t_R = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$



WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES $t_R = t_F = 2.5 \text{ ns}$, 10% to 90%; f = 1 MHz; $t_W = 500 \text{ ns}$

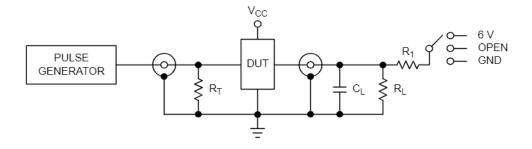


| | V _{CC} | | | | | |
|-----------------|-------------------------|-------------------------|--------------------------|--|--|--|
| Symbol | 3.3 V \pm 0.3 V | 2.7 V | 2.5 V \pm 0.2 V | | | |
| Vmi | 1.5 V | 1.5 V | V _{CC} /2 | | | |
| Vmo | 1.5 V | 1.5 V | V _{CC} /2 | | | |
| V _{HZ} | V _{OL} + 0.3 V | V _{OL} + 0.3 V | V _{OL} + 0.15 V | | | |
| V_{LZ} | V _{OH} – 0.3 V | V _{OH} - 0.3 V | V _{OH} – 015 V | | | |

WAVEFORM 3 - LE to On PROPAGATION DELAYS, LE MINIMUM PULSE WIDTH, Dn to LE SETUP AND HOLD TIMES

 t_{R} = t_{F} = 2.5 ns, 10% to 90%; f = 1 MHz; t_{W} = 500 ns except when noted

Figure 3. AC Waveforms



| TEST | SWITCH |
|--|--|
| t _{PLH} , t _{PHL} | Open |
| t _{PZL} , t _{PLZ} | 6 V at V _{CC} = 3.3 ± 0.3 V 6 V at V _{CC} = 2.5 ± 0.2 V |
| Open Collector/Drain t _{PLH} and t _{PHL} | 6 V |
| t _{PZH} , t _{PHZ} | GND |

 C_L = 50 pF at V_{CC} = 3.3 ± 0.3 V or equivalent (includes jig and probe capacitance) C_L = 30 pF at V_{CC} = 2.5 ± 0.2 V or equivalent (includes jig and probe capacitance) R_L = R_1 = 500 Ω or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 4. Test Circuit

ORDERING INFORMATION

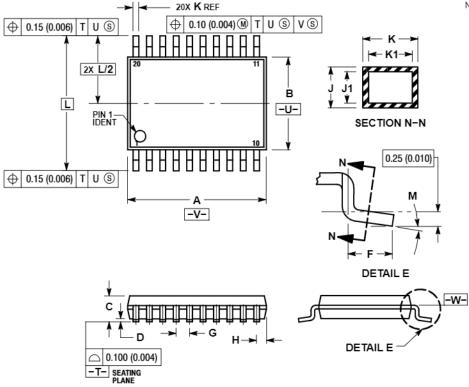
| Device | Package | Shipping [†] |
|-------------------|-------------------------|-----------------------|
| MC74LCX373DWR2G | SOIC-20 WB (Pb-Free) | 1000 Tape & Reel |
| MC74LCX373DTG | TSSOP-20 (Pb-Free) | 75 Units / Rail |
| MC74LCX373DTR2G | TSSOP-20 (Pb-Free) | 2500 Tape & Reel |
| NLV74LCX373DTR2G* | TSSOP-20 (Pb-Free) | 2500 Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP

Capable.

PACKAGE DIMENSIONS

TSSOP-20 DT SUFFIX CASE 948E-02 ISSUE C



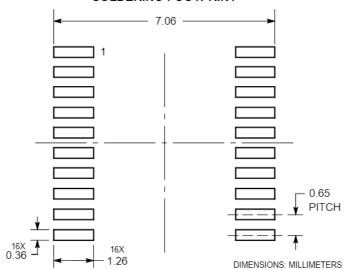
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDF SIDE.
 - SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER CIPIC.
 - SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08
 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.
 - CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

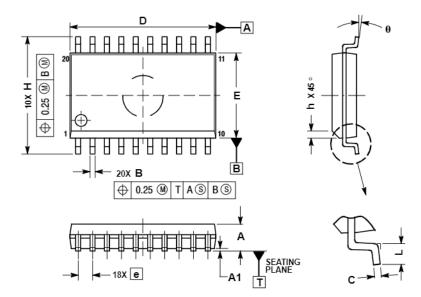
| | MILLIN | IETERS | INC | HES |
|-----|--------|--------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 6.40 | 6.60 | 0.252 | 0.260 |
| В | 4.30 | 4.50 | 0.169 | 0.177 |
| С | | 1.20 | | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 | BSC | 0.026 BSC | |
| Н | 0.27 | 0.37 | 0.011 | 0.015 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 | | 0.252 | BSC |
| М | 0° | 8° | 0° | 8° |

SOLDERING FOOTPRINT



PACKAGE DIMENSIONS

SOIC-20 WB CASE 751D-05 ISSUE G



NOTES

- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES
 PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE. MACINION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

| | MILLIMETERS | |
|-----|-------------|-------|
| DIM | MIN | MAX |
| Α | 2.35 | 2.65 |
| A1 | 0.10 | 0.25 |
| В | 0.35 | 0.49 |
| С | 0.23 | 0.32 |
| D | 12.65 | 12.95 |
| Е | 7.40 | 7.60 |
| е | 1.27 BSC | |
| Н | 10.05 | 10.55 |
| h | 0.25 | 0.75 |
| L | 0.50 | 0.90 |
| θ | 0° | 7° |

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